



## **GP1M018A020HG Information**



For Reference Only

Part Number GP1M018A020HG

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 200V 18A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **GP1M018A020HG Specifications**

Manufacturer Part Number         GPIM018A020HG           Manufacturer         Global Power Technologies Group           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         200V           Current - Continuous Drain (Id) @ 25°C         18A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         94W (Tc)           Rds On (Max) @ Id, Vgs         170 mOhm @ 9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220           Package / Case         TO-220-3		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3  Series  - FET Type  N-Channel  Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Prive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  170 mOhm @ 9A, 10V  Operating Temperature  MosfET (Netal Oxide)  Drive Voltage (Metal Oxide)  18A (Tc)  10V  Vg (250µA  18n C@ 10V  190V  190V	Manufacturer Part Number	GP1M018A020HG
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         200V           Current - Continuous Drain (Id) @ 25°C         18A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         94W (Tc)           Rds On (Max) @ Id, Vgs         170 mOhm @ 9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220           Package / Case         TO-220-3	Manufacturer	Global Power Technologies Group
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds950pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)94W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
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Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
I .		Report errors?

### **GP1M018A020HG Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **GP1M018A020HG Payment Methods**



















## **GP1M018A020HG Shipping Methods**













If you have any question about GP1M018A020HG, please do not hesitate to contact us!

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